

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L2	114736 2	semiconductor	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_TD B	2002/09/29 13:31
2	BRS	L17	12337	align\$5 adj1 marks	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_TD B	2002/09/29 13:41
3	BRS	L31	5749	2 and 17	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_TD B	2002/09/29 13:40
4	BRS	L38	3286	31 and (trench\$3 or hol\$3 or open\$4 or vias)	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_TD B	2002/09/29 13:41
5	BRS	L45	2995	38 and (first or second or region)	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_TD B	2002/09/29 13:43

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L52	656	45 and scatter\$4	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_TD B	2002/09/29 13:43
7	BRS	L59	554	52 and (block\$4 or planar\$7 or metal)	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_TD B	2002/09/29 13:48

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L8	1105	LSA or (laserlight adj1 scattering adj1 alignment)	USPAT; EPO; JPO; DERW ENT; IBM_TD B	2002/09/29 15:04
2	BRS	L14	684	8 and (trench\$3 or hol\$3 or open\$3)	USPAT; EPO; JPO; DERW ENT; IBM_TD B	2002/09/29 15:09
3	BRS	L20	307	14 and (metal\$6)	USPAT; EPO; JPO; DERW ENT; IBM_TD B	2002/09/29 15:12
4	BRS	L26	171	20 and (scan\$4)	USPAT; EPO; JPO; DERW ENT; IBM_TD B	2002/09/29 15:12
5	BRS	L32	165	26 and (laser or light or scatter\$4 or align\$5 or mark or region)	USPAT; EPO; JPO; DERW ENT; IBM_TD B	2002/09/29 15:14
6	BRS	L38	165	32 and (first or second or thickness or angstrom)	USPAT; EPO; JPO; DERW ENT; IBM_TD B	2002/09/29 15:14

	Type	L #	Hits	Search Text	DBs	Time Stamp
7	BRS	L44	147	38 and (block\$5 or seed\$6)	USPAT; EPO; JPO; DERW ENT; IBM_TDB	2002/09/29 15:15
8	BRS	L50	146	44 and (etch\$5 or pattern\$5 or expos\$5)	USPAT; EPO; JPO; DERW ENT; IBM_TDB	2002/09/29 15:17
9	BRS	L56	142	50 and (wafer or silicon or nitride)	USPAT; EPO; JPO; DERW ENT; IBM_TDB	2002/09/29 15:18
10	BRS	L62	447774	contrast	USPAT; EPO; JPO; DERW ENT; IBM_TDB	2002/09/29 15:19
11	BRS	L80	111330 5	semiconductor	USPAT; EPO; JPO; DERW ENT; IBM_TDB	2002/09/29 15:21
12	BRS	L86	133	56 and 80	USPAT; EPO; JPO; DERW ENT; IBM_TDB	2002/09/29 15:20

	Type	L #	Hits	Search Text	DBs	Time Stamp
13	BRS	L98	53024	62 and 80	USPAT; EPO; JPO; DERW ENT; IBM_TD B	2002/09/29 15:22
14	BRS	L104	26	86 and 62	USPAT; EPO; JPO; DERW ENT; IBM_TD B	2002/09/29 15:22
15	BRS	L110	35125	lithography	USPAT; EPO; JPO; DERW ENT; IBM_TD B	2002/09/29 15:23
16	BRS	L116	23	104 and 110	USPAT; EPO; JPO; DERW ENT; IBM_TD B	2002/09/29 15:23

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L8	1105	LSA or (laserlight adj1 scattering adj1 alignment)	USPAT; EPO; JPO; DERW ENT; IBM_TD B	2002/09/29 15:04
2	BRS	L14	684	8 and (trench\$3 or hol\$3 or open\$3)	USPAT; EPO; JPO; DERW ENT; IBM_TD B	2002/09/29 15:56
3	BRS	L20	307	14 and (metal\$6)	USPAT; EPO; JPO; DERW ENT; IBM_TD B	2002/09/29 15:12
4	BRS	L62	447774	contrast	USPAT; EPO; JPO; DERW ENT; IBM_TD B	2002/09/29 15:59
5	BRS	L80	111330 5	semiconductor	USPAT; EPO; JPO; DERW ENT; IBM_TD B	2002/09/29 15:21
6	BRS	L110	35125	lithography	USPAT; EPO; JPO; DERW ENT; IBM_TD B	2002/09/29 15:23

	Type	L #	Hits	Search Text	DBs	Time Stamp
7	BRS	L56	142	50 and (wafer or silicon or nitride)	USPAT; EPO; JPO; DERW ENT; IBM_T B	2002/09/29 15:33
8	BRS	L122	119	56 not 116	USPAT; EPO; JPO; DERW ENT; IBM_T B	2002/09/29 15:34
9	BRS	L128	264	20 and (laser or light or scatter\$4 or align\$5 or mark or region)	USPAT; EPO; JPO; DERW ENT; IBM_T B	2002/09/29 15:39
10	BRS	L134	262	128 and (first or second or thickness or angstrom)	USPAT; EPO; JPO; DERW ENT; IBM_T B	2002/09/29 15:40
11	BRS	L140	211	134 and (block\$5 or seed\$6)	USPAT; EPO; JPO; DERW ENT; IBM_T B	2002/09/29 15:42
12	BRS	L147	191	140 and (etch\$5 or pattern\$5 or expos\$5)	USPAT; EPO; JPO; DERW ENT; IBM_T B	2002/09/29 15:44

	Type	L #	Hits	Search Text	DBs	Time Stamp
13	BRS	L153	33	62 and 147	USPAT; EPO; JPO; DERW ENT; IBM_TDB	2002/09/29 15:55
14	BRS	L159	27	80 and 153	USPAT; EPO; JPO; DERW ENT; IBM_TDB	2002/09/29 15:47
15	BRS	L165	159	80 and 147	USPAT; EPO; JPO; DERW ENT; IBM_TDB	2002/09/29 15:55
16	BRS	L171	159	165 and (trench\$3 or hol\$3 or open\$3)	USPAT; EPO; JPO; DERW ENT; IBM_TDB	2002/09/29 15:57
17	BRS	L177	27	171 and 62	USPAT; EPO; JPO; DERW ENT; IBM_TDB	2002/09/29 16:00
18	BRS	L183	22	177 and (silicon or nitride)	USPAT; EPO; JPO; DERW ENT; IBM_TDB	2002/09/29 16:02